

Technological Comparison Table between M5M51008B* and M5M5V108C

Circuit	M5M51008B	M5M5V108C
Memory Cell	High Resistance Type	TFT Load Type
Peripheral Circuit	CMOS	CMOS

Process	M5M51008B	M5M5V108C
Wafer Process	Triple Poly +Single Al	Quadruple Poly +Double Al
Design Rule	0.6μm	0.4μm
Gate Oxide	SiO ₂ (10nm)	SiO ₂ (10nm)
Transistor Type	LDD	LDD
Word Line	WSi	WSi
Bit Line	Al	Al

Assembly	M5M51008B	M5M5V108C
Plastic Material	Epoxy - resign	Epoxy - resign
Lead Frame Material	Fe - Ni 42 alloy	Fe - Ni 42 alloy
Lead Frame Finish	Sn/Pb Plating	Sn/Pb Plating
Wire Bond Material	Au	Au
Die Bond Material	Soft Solder	Resign

Factory	M5M51008B	M5M5V108C
Wafer Process	KOCHI	KOCHI
Assembly / Test	KUMAMOTO	KUMAMOTO, CHINA

* : -70/10/12/15VL,VLL

Technological Comparison Table between M5M51008B** and M5M51008C

Circuit	M5M51008B	M5M51008C
Memory Cell	High Resistance Type	TFT Load Type
Peripheral Circuit	CMOS	CMOS

Process	M5M51008B	M5M51008C
Wafer Process	Triple Poly +Single Al	Quadruple Poly +Double Al
Design Rule	0.6μm	0.4μm
Gate Oxide	SiO ₂ (14nm)	SiO ₂ (12nm)
Transistor Type	LDD	LDD
Word Line	WSi	WSi
Bit Line	Al	Al

Assembly	M5M51008B	M5M51008C
Plastic Material	Epoxy - resign	Epoxy - resign
Lead Frame Material	Fe - Ni 42 alloy	Fe - Ni 42 alloy
Lead Frame Finish	Sn/Pb Plating	Sn/Pb Plating
Wire Bond Material	Au	Au
Die Bond Material	Soft Solder	Resign

Factory	M5M51008B	M5M51008C
Wafer Process	KOCHI	KOCHI
Assembly / Test	KUMAMOTO	KUMAMOTO, CHINA

** : -55/70/10L,LL